

MMDT5451

COMPLEMENTARY NPN / PNP SMALL SIGNAL TRANSISTOR IN SOT363

Features

- **Epitaxial Planar Die Construction**
- Complementary Pair: 1 5551 Type NPN

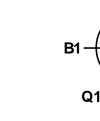
1 5401 Type PNP

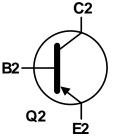
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

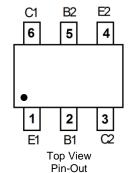
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish. Solderable per MIL-STD-202, Method 208 **@3**
- Weight: 0.006 grams (Approximate)









Top View

Device Symbol

Ordering Information (Note 4)

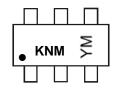
Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
MMDT5451-7-F	AEC-Q101	KNM	7	8	3,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

E1

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



KNM = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018)M = Month (ex: 9 = September)

Date Code Key

Date Code Ne	- y											
Year	2017	20	18	2019	2020	20	21	2022	2023	20	24	2025
Code	E	F	=	G	Н		I	J	K	I	_	М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

MMDT5451 Document Number: DS30171 Rev: 10 - 2



Absolute Maximum Ratings – NPN 5551 Section (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	180	V
Collector-Emitter Voltage	V _{CEO}	160	V
Emitter-Base Voltage	V _{EBO}	6	V
Continuous Collector Current	Ic	200	mA

Absolute Maximum Ratings - PNP 5401 Section (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-160	V
Collector-Emitter Voltage	V _{CEO}	-150	V
Emitter-Base Voltage	V _{EBO}	-6	V
Continuous Collector Current	Ic	-200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Dower Dissination	(Note 5)	Б	200	mW	
Power Dissipation	(Notes 6 & 7)	P_D	320	IIIVV	
Thermal Resistance, Junction to Ambient	(Note 5)	D	625		
Thermal Resistance, Junction to Ambient	(Notes 6 & 7)	$R_{\theta JA}$	390	°C/W	
Thermal Resistance, Junction to Case	R _θ JC	140			
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Notes:

^{5.} For a device mounted on minimum recommended pad layout 1oz weight copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

^{6.} Same as Note 5, except the device is mounted on 25mm X 25mm 2oz copper.

^{7.} Maximum combined dissipation.

^{8.} Thermal resistance from junction to the top of package.



Electrical Characteristics - NPN 5551 Section (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Collector-Base Breakdown Voltage	BV _{CBO}	180	_		V	$I_C = 100\mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	160	_	_	V	$I_C = 1mA, I_B = 0$	
Emitter-Base Breakdown Voltage	BV _{EBO}	6		_	>	$I_E = 10\mu A, I_C = 0$	
Collector-Base Cutoff Current	1	_		50	nA	$V_{CB} = 120V, I_E = 0$	
Collector-Base Cuton Current	ICBO	_		50	μΑ	$V_{CB} = 120V, I_E = 0, T_A = +100$ °C	
Base-Emitter Cutoff Current	I _{EBO}	_	_	50	nA	$V_{EB} = 4V, I_C = 0$	
ON CHARACTERISTICS (Note 9)							
		80		_		I _C = 1.0mA, V _{CE} = 5.0V	
DC Current Gain	h _{FE}	80	_	250	_	$I_C = 10mA, V_{CE} = 5.0V$	
		30		_		I _C = 50mA, V _{CE} = 5.0V	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_		0.15	V	I _C = 10mA, I _B = 1.0mA	
Conector-Enniter Saturation Voltage			_	0.20	٧	$I_C = 50mA$, $I_B = 5.0mA$	
Base-Emitter Saturation Voltage	V			1.0	V	I _C = 10mA, I _B = 1.0mA	
Base-Effiller Saturation Voltage	$V_{BE(SAT)}$					$I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$	
SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	C_{obo}	_	_	6.0	pF	$V_{CB} = 10V$, $f = 1.0MHz$, $I_E = 0$	
Small Signal Current Gain	h _{fe}	50	_	250		$I_C = 1mA, V_{CE} = 10V, f = 1.0MHz$	
Current Gain-Bandwidth Product	f_{T}	100		300	MHz	$I_C = 10mA$, $V_{CE} = 10V$, $f = 100MHz$	
Noise Figure	NF	_		8.0	dB	$V_{CE} = 5.0V$, $I_C = 200\mu A$, $R_S = 1k\Omega$, $f = 1.0kHz$	

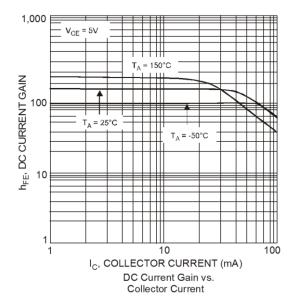
Electrical Characteristics - PNP 5401 Section (@TA = +25°C, unless otherwise specified.)

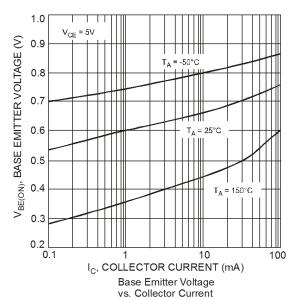
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Collector-Base Breakdown Voltage	BV _{CBO}	-160	_	_	V	$I_C = -100\mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-150	_	_	V	$I_C = -1 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BV _{EBO}	-6	_	_	V	$I_E = -10\mu A, I_C = 0$	
Collector-Base Cutoff Current	1	_		-50	nA	V _{CB} = -120V, I _E = 0	
Collector-Base Cuton Current	I _{CBO}	_	_	-50	μA	V _{CB} = -120V, I _E = 0, T _A = +100°C	
Base-Emitter Cutoff Current	I _{EBO}	_	_	-50	nA	V _{EB} = -4V, I _C = 0	
ON CHARACTERISTICS (Note 9)							
		50				$I_C = -1.0 \text{mA}, V_{CE} = -5.0 \text{V}$	
DC Current Gain	h _{FE}	60	_	240	_	$I_C = -10 \text{mA}, V_{CE} = -5.0 \text{V}$	
		50				$I_C = -50 \text{mA}, V_{CE} = -5.0 \text{V}$	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}			-0.20	V	$I_C = -10mA$, $I_B = -1.0mA$	
Collector-Emitter Saturation Voltage			_	-0.50	V	$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$	
Base-Emitter Saturation Voltage	\/			-1.0	V	$I_C = -10mA$, $I_B = -1.0mA$	
Base-Emilier Saturation Voltage	V _{BE(SAT)}	_		-1.0	V	$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$	
SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	C_{obo}	_	_	6.0	pF	$V_{CB} = -10V$, $f = 1.0MHz$, $I_E = 0$	
Small Signal Current Gain	h _{fe}	40		260		$I_C = -1mA$, $V_{CE} = -10V$, $f = 1.0MHz$	
Current Gain-Bandwidth Product	f⊤	100		300	MHz	$I_C = -10mA$, $V_{CE} = -10V$, $f = 100MHz$	
Noise Figure	NF	_		8.0	dB	$V_{CE} = -5.0V$, $I_{C} = -200\mu A$, $R_{S} = 1\Omega$, $f = 1.0kHz$	

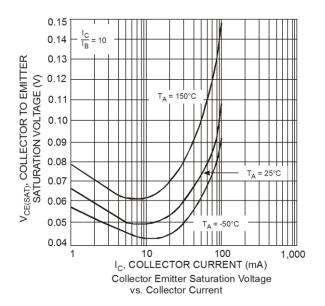
Note: 9. Measured under pulsed conditions. Pulse width $\leq 300 \mu s.$ Duty cycle $\leq 2\%.$

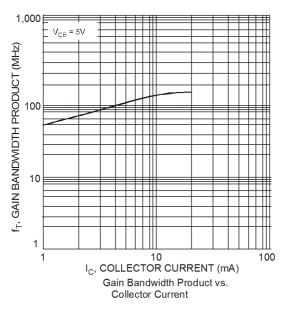


Typical Electrical Characteristics - NPN 5551 Section (@TA = +25°C, unless otherwise specified.)



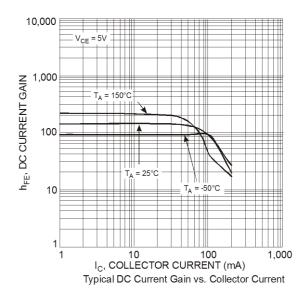


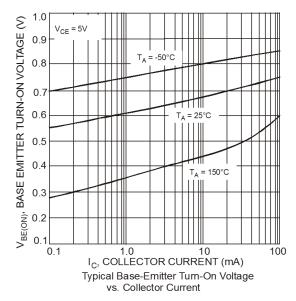


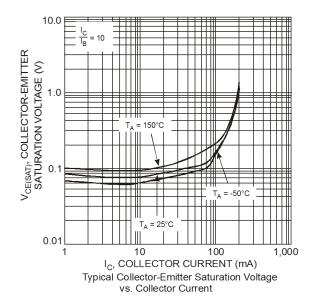


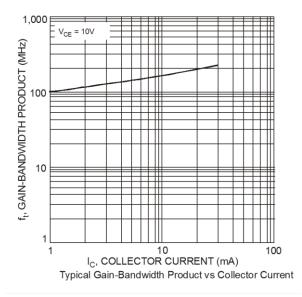


Typical Electrical Characteristics - PNP 5401 Section (@TA = +25°C, unless otherwise specified.)







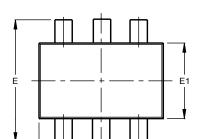


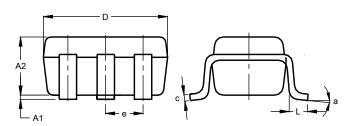
June 2018



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.





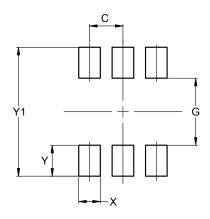
SOT363							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.10	0.30	0.25				
C	0.10	0.22	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	0.650 BSC						
F	0.40	0.45	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363

SOT363



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Υ	0.600
Y1	2.500

For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking. Note:



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